## **Glow Discharge Prod**

SPUTTERING AND PLASMA ETCHING

**Brian Chapman** 

A WILEY-INTERSCIENCE PUBLICATION

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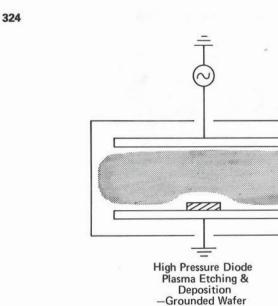


Figure 7-23. High pressure diode plasma etching and dep

quarter of the applied rf peak-to-peak voltage (Chapter -250 V for practical plasma etching processes. This is a measurements and by observation of the dark spaces for energy of ion bombardment on an electrode is determined by collisions in the sheath, as discussed in Chapters

Reactive ion etching systems (Figure 7-24) are essenti systems. In sputtering, intense ion bombardment at the nowhere else. This is achieved by making the target area of the grounded chamber and baseplate. As a result, the very small, but the sheath at the target, and hence at the rf peak-to-peak, amounting typically to -300 V.

The different operating pressures of the two diode systemce ion bombardment energies very greatly, because the collisions per unit length at the higher pressure is offset much thinner dark space sheath. The two effects would

